

Norihiro Hoshino

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Fast growth of n-type 4H-SiC bulk crystal by gas-source method. Journal of Crystal Growth, 2017, 478, 9-16.	1.5	16
2	High-speed, high-quality crystal growth of 4H-SiC by high-temperature gas source method. Applied Physics Express, 2014, 7, 065502.	2.4	15
3	Stable and high-speed SiC bulk growth without dendrites by the HTCVD method. Journal of Crystal Growth, 2016, 448, 29-35.	1.5	11
4	Developing Technologies of SiC Gas Source Growth Method. Materials Science Forum, 2016, 858, 23-28.	0.3	9
5	Reduction in dislocation densities in 4H-SiC bulk crystal grown at high growth rate by high-temperature gas-source method. Applied Physics Express, 2020, 13, 095502.	2.4	9
6	Development of 150-mm 4H-SiC Substrates Using a High-Temperature Chemical Vapor Deposition Method. Materials Science Forum, 0, 1004, 14-19.	0.3	7
7	Doping Fluctuation and Defect Formation in Fast 4H-SiC Crystal Growth Using a High-Temperature Gas Source Method. Materials Science Forum, 0, 858, 61-64.	0.3	6
8	Fast 4H-SiC Bulk Growth by High-Temperature Gas Source Method. Materials Science Forum, 0, 1004, 5-13.	0.3	4
9	Investigation of propagation and coalescence of threading screw and mixed dislocations in 4H-SiC crystals grown by the high-temperature gas source method. Journal of Crystal Growth, 2022, 590, 126676.	1.5	4